

MOS INTEGRATED CIRCUIT μ PD4416004

16M-BIT CMOS FAST SRAM 4M-WORD BY 4-BIT

Description

The μ PD4416004 is a high speed, low power, 16,777,216 bits (4,194,304 words by 4 bits) CMOS static RAM. Operating supply voltage is 3.3 V ± 0.3 V.

The μ PD4416004 is packaged in a 54-PIN PLASTIC TSOP (II).

Features

- 4,194,304 words by 4 bits
- Fast access time : 15, 17 ns (MAX.)
- Output Enable input for easy application

Ordering Information

	Part number	t number Package		Access time	Supply curre	nt (MAX.)	
			V	(MAX.) ns	At operating mA	At standby mA	
*	μPD4416004G5-A15-9JF	54-PIN PLASTIC TSOP (II)	3.3 ± 0.3	15	220	10	
*	μPD4416004G5-A17-9JF	(10.16 mm (400))		17	210		

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The mark \star shows major revised points.

Pin Configuration (Marking Side)

/xxx indicates active low signal.

			1
NC ()	1	54	
Vcc O	2	53	
NC 0	3	52	NC
NC 0	4	51	NC
GND O	5	50	O Vcc
I/O 4 ○ < →	6	49	 →○ I/O 3
A0 ○>	7	48	→ A21
A1 O	8	47	<○ A20
A2 O>	9	46	<○ A19
A3 O≻	10	45	<⊖ A18
A4 O>	11	44	<⊖ A17
A5 O	12	43	O NC
/CS ○>	13	42	<○ /OE
Vcc O	14	41	GND
/WE O──►	15	40	——————————————————————————————————————
NC O	16	39	<○ A16
A6 O	17	38	→ → ○ A15
A7 O►	18	37	→ ○ A14
A8 O≻	19	36	→ → ○ A13
A9 O≻	20	35	<⊖ A12
A10 O>	21	34	→ () A11
I/O 1 O ∢ →	22	33	←→ ○ I/O 2
Vcc O	23	32	GND
NC O	24	31	O NC
NC O	25	30	O NC
GND O	26	29	——————————————————————————————————————
NC O	27	28	O NC
l			J

54-PIN PLASTIC TSOP (II) (10.16 mm (400))
[µPD4416004G5–xxx–9JF]

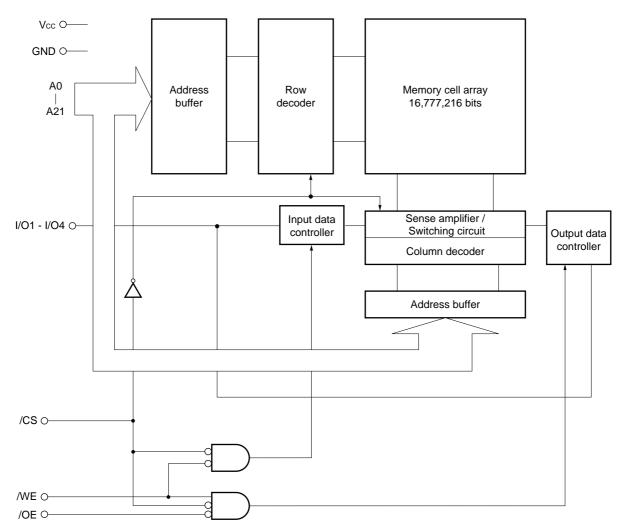
A0 - A21	: Address Inputs
I/O1 - I/O4	: Data Inputs / Outputs
/CS	: Chip Select
/WE	: Write Enable
/OE	: Output Enable
Vcc	: Power supply
GND	: Ground
NC	: No connection
IC	: Internal connection Note

Note Leave this pin connect to GND.

Remark Refer to Package Drawing for 1-pin index mark.

NEC

Block Diagram



Truth Table

/CS	/OE	/WE	Mode	I/O	Supply current
н	×	×	Not selected	High impedance	lsв
L	L	Н	Read	Dout	lcc
L	×	L	Write	Din	
L	Н	Н	Output disable	High impedance	

Remark ×: Don't care

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Electrical Specifications

Absolute Maximum Ratings

	Parameter	Symbol	Condition	Rating	Unit
*	Supply voltage	Vcc		-0.5 ^{Note} to +4.0	V
*	Input / Output voltage	Vт		-0.5 ^{Note} to +4.0	V
	Operating ambient temperature	TA		0 to 70	°C
	Storage temperature	Tstg		-55 to +125	°C

Note -2.0 V (MIN.) (pulse width : 2 ns)

Caution Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	Vcc		3.0	3.3	3.6	V
High level input voltage	Vін		2.0		Vcc + 0.3	V
Low level input voltage	VIL		-0.3 Note		+0.8	V
Operating ambient temperature	TA		0		70	°C

Note -2.0 V (MIN.) (pulse width : 2 ns)

DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

Parameter	Symbol	Test condit	ion	MIN.	TYP.	MAX.	Unit
Input leakage current	lu	VIN = 0 V to Vcc		-2		+2	μΑ
Output leakage current	ILO	$V_{I/O} = 0 V$ to Vcc, $/CS = V_{IH} O$ $/WE = V_{IL}$	-2		+2	μA	
Operating supply current	Icc	/CS = VIL, II/O = 0 mA,	Cycle time : 15 ns			220	mA
		Minimum cycle time	Cycle time : 17 ns			210	
Standby supply current	lsв	/CS = VIH, VIN = VIH or VIL, M	inimum cycle time			80	mA
	ISB1	$/CS \ge V_{CC} - 0.2 V$,				10	
		$V_{\text{IN}} \leq 0.2 \text{ V}$ or $V_{\text{IN}} \geq V_{\text{CC}} - 0.2$	$V_{\text{IN}} \leq 0.2 \text{ V}$ or $V_{\text{IN}} \geq V_{\text{CC}} - 0.2 \text{ V}$				
High level output voltage	Vон	Iон = -4.0 mA		2.4			V
Low level output voltage	Vol	loL = +8.0 mA				0.4	V

Remark VIN : Input voltage, VI/O : Input / Output voltage

Capacitance (TA = 25 °C, f = 1 MHz)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	CIN	$V_{IN} = 0 V$			6	pF
Input / Output capacitance	Cı/o	$V_{I/O} = 0 V$			8	pF

Remarks 1. VIN : Input voltage, VI/O : Input / Output voltage

2. These parameters are periodically sampled and not 100% tested.

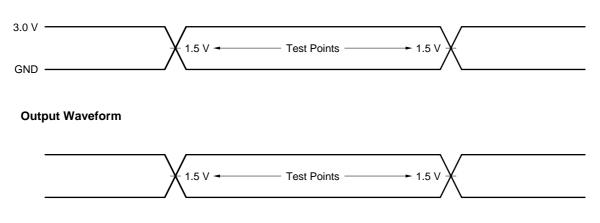
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AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

AC Test Conditions

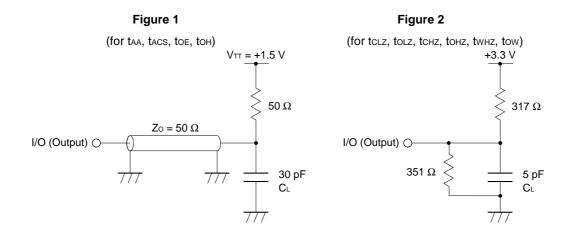
LVTTL Interface

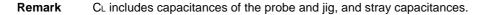
Input Waveform (Rise and Fall Time \leq 3 ns)



Output Load

AC characteristics directed with the note should be measured with the output load shown in Figure 1 or Figure 2.





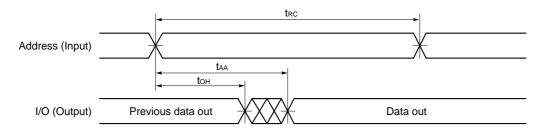
Read Cycle

Parameter	Symbol	-A	.15	-A17		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
Read cycle time	trc	15		17		ns	
Address access time	taa		15		17	ns	1
/CS access time	tacs		15		17	ns	
/OE access time	toe		7		8	ns	
Output hold from address change	tон	3		3		ns	
/CS to output in low impedance	tcLz	3		3		ns	2, 3
/OE to output in low impedance	tolz	0		0		ns	
/CS to output in high impedance	tснz		7		8	ns	
/OE to output hold in high impedance	tонz		7		8	ns	

Notes 1. See the output load shown in Figure 1.

- 2. Transition is measured at ± 200 mV from steady-state voltage with the output load shown in Figure 2.
- 3. These parameters are periodically sampled and not 100% tested.

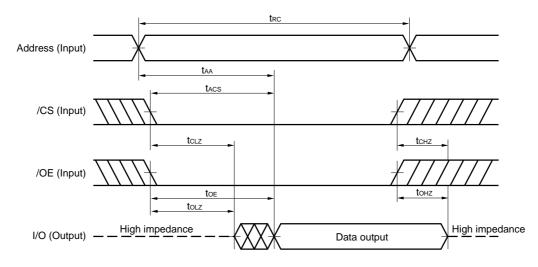
Read Cycle Timing Chart 1 (Address Access)



Remarks 1. In read cycle, /WE should be fixed to high level.

2. /CS = /OE = VIL

Read Cycle Timing Chart 2 (/CS Access)



Caution Address valid prior to or coincident with /CS low level input.

Remark In read cycle, /WE should be fixed to high level.

Write Cycle

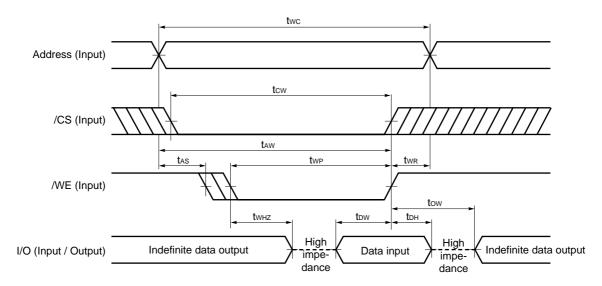
*

Parameter	Symbol	-A	15	-A17		Unit	Notes
		MIN.	MAX.	MIN.	MAX.		
Write cycle time	twc	15		17		ns	
/CS to end of write	tcw	10		11		ns	
Address valid to end of write	taw	10		11		ns	
Write pulse width	twp	10		11		ns	
Data valid to end of write	tow	7		8		ns	
Data hold time	tон	0		0		ns	
Address setup time	tas	0		0		ns	
Write recovery time	twr	1		1		ns	
/WE to output in high impedance	twнz		7		8	ns	1, 2
Output active from end of write	tow	3		3		ns	

Notes 1. Transition is measured at \pm 200 mV from steady-state voltage with the output load shown in Figure 2.

2. These parameters are periodically sampled and not 100% tested.

Write Cycle Timing Chart 1 (/WE Controlled)



Cautions 1. /CS or /WE should be fixed to high level during address transition.

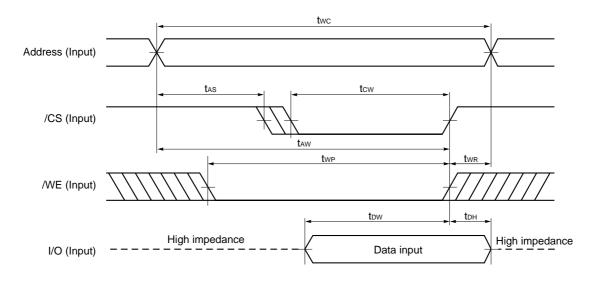
2. Do not input data to the I/O pins while they are in the output state.

Remarks 1. Write operation is done during the overlap time of a low level /CS, a low level /WE.

- 2. During twHz, I/O pins are in the output state, therefore the input signals of opposite phase to the output must not be applied.
- **3.** When /WE is at low level, the I/O pins are always high impedance. When /WE is at high level, read operation is executed. Therefore /OE should be at high level to make the I/O pins high impedance.

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Write Cycle Timing Chart 2 (/CS Controlled)

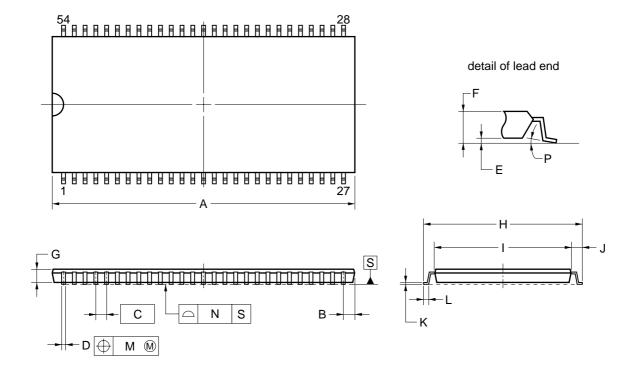


Cautions 1. /CS or /WE should be fixed to high level during address transition.2. Do not input data to the I/O pins while they are in the output state.

Remark Write operation is done during the overlap time of a low level /CS and a low level /WE.

Package Drawing

54-PIN PLASTIC TSOP (II) (10.16 mm (400))



NOTES

- 1. Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.
- Dimension "A" does not include mold fiash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per side.

ITEM	MILLIMETERS
A	22.22±0.05
В	0.91 MAX.
С	0.80 (T.P.)
D	$0.32\substack{+0.08\\-0.07}$
E	0.10±0.05
F	1.1±0.1
G	1.00
Н	11.76±0.20
I	10.16±0.10
J	0.80±0.20
к	$0.145\substack{+0.025\\-0.015}$
L	0.50±0.10
М	0.13
Ν	0.10
Р	3° ^{+7°} 3°
	S54G5-80-9JF-2

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD4416004.

Type of Surface Mount Device

μPD4416004 : 54-PIN PLASTIC TSOP (II) (10.16 mm (400))

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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M8E 00.4